

*New Jersey Semi-Conductor Products, Inc.*

20 STERN AVE.  
SPRINGFIELD, NEW JERSEY 07081  
U.S.A.

TELEPHONE: (973) 376-2922  
(212) 227-8006  
FAX: (973) 376-8980

# 2N3565 • PN3565

NPN LOW LEVEL HIGH GAIN AMPLIFIERS  
DIFFUSED SILICON PLANAR\* EPITAXIAL TRANSISTORS

- $P_D \dots 625 \text{ mW} @ T_A = 25^\circ\text{C}$
- $hFE \dots 150 - 600 @ 1.0 \text{ mA}$
- $V_{CEO} \dots 25 \text{ V (MIN)}$

**ABSOLUTE MAXIMUM RATINGS (Note 1)**

**Maximum Temperatures**

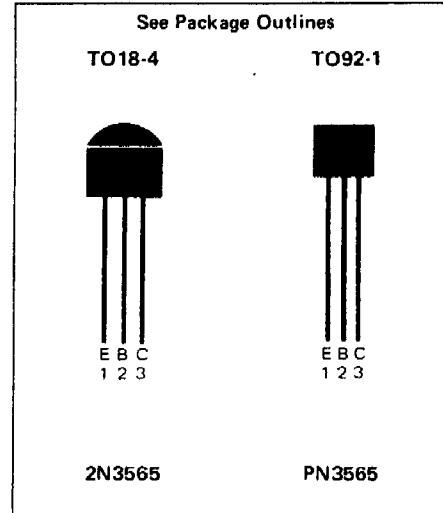
	2N3565	PN3565
Storage Temperature	-55°C to +125°C	-55°C to +150°C
Operating Junction Temperature	125°C	150°C
Lead Temperature	260°C	260°C

**Maximum Power Dissipation (Note 2)**

Total Dissipation at 25°C Case Temperature	0.5 W	1.0 W
at 65°C Case Temperature	0.3 W	
at 25°C Ambient Temperature	0.2 W	0.625 W

**Maximum Voltages and Current**

$V_{CBO}$	Collector to Base Voltage	30 V	30 V
$V_{CEO}$	Collector to Emitter Voltage (Note 3)	25 V	25 V
$V_{EBO}$	Emitter to Base Voltage	6.0 V	6.0 V
$I_C$	Collector Current	50 mA	50 mA



**ELECTRICAL CHARACTERISTICS (25°C Ambient Temperature unless otherwise noted)**

SYMBOL	CHARACTERISTIC	MIN.	MAX.	UNITS	TEST CONDITIONS
$hFE$	DC Current Gain	150	600		$I_C = 1.0 \text{ mA}, V_{CE} = 10 \text{ V}$
$hFE$	DC Current Gain	70			$I_C = 100 \mu\text{A}, V_{CE} = 10 \text{ V}$
$h_f$	High Frequency Current Gain	2.0	12		$I_C = 1.0 \text{ mA}, V_{CE} = 5.0 \text{ V}, f = 20 \text{ MHz}$
$\beta V_{CE(\text{sat})}$	Collector Saturation Voltage		0.35	V	$I_C = 1.0 \text{ mA}, I_B = 0.1 \text{ mA}$
$I_{CBO}$	Collector Cutoff Current		50	nA	$I_E = 0, V_{CB} = 25 \text{ V}$
$\beta I_{CBO}$	Collector Cutoff Current		3.0	$\mu\text{A}$	$I_E = 0, V_{CB} = 25 \text{ V}, T_A = 65^\circ\text{C}$
$C_{ob}$	Open Circuit Output Capacitance		4.0	pF	$I_E = 0, V_{CB} = 5.0 \text{ V}, f = 140 \text{ kHz}$
$BV_{CBO}$	Collector to Base Breakdown Voltage	30		V	$I_E = 0, I_C = 100 \mu\text{A}$
$V_{CEO(sus)}$	Collector to Emitter Sustaining Voltage	25		V	$I_B = 0, I_C = 2.0 \text{ mA}$
$BV_{EBO}$	Emitter to Base Breakdown Voltage	6.0		V	$I_C = 0, I_E = 10 \mu\text{A}$
$h_{ie}$	Input Resistance	2.0	20	k $\Omega$	$I_C = 1.0 \text{ mA}, V_{CE} = 5.0 \text{ V}, f = 1.0 \text{ kHz}$
$h_{oe}$	Output Conductance	0.5	100	$\mu\text{mhos}$	$I_C = 1.0 \text{ mA}, V_{CE} = 5.0 \text{ V}, f = 1.0 \text{ kHz}$
$h_{fe}$	Small Signal Current Gain	120	750		$I_C = 1.0 \text{ mA}, V_{CE} = 5.0 \text{ V}, f = 1.0 \text{ kHz}$